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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

| | |
|--------------------------------|---|
| Product Status | Active |
| Number of LABs/CLBs | - |
| Number of Logic Elements/Cells | - |
| Total RAM Bits | 36864 |
| Number of I/O | 71 |
| Number of Gates | 125000 |
| Voltage - Supply | 1.425V ~ 1.575V |
| Mounting Type | Surface Mount |
| Operating Temperature | -20°C ~ 85°C (TJ) |
| Package / Case | 100-TQFP |
| Supplier Device Package | 100-VQFP (14x14) |
| Purchase URL | https://www.e-xfl.com/product-detail/microchip-technology/a3pn125-vqg100 |

Core Architecture

VersaTile

The proprietary IGLOO and ProASIC3 device architectures provide granularity comparable to gate arrays. The device core consists of a sea-of-VersaTiles architecture.

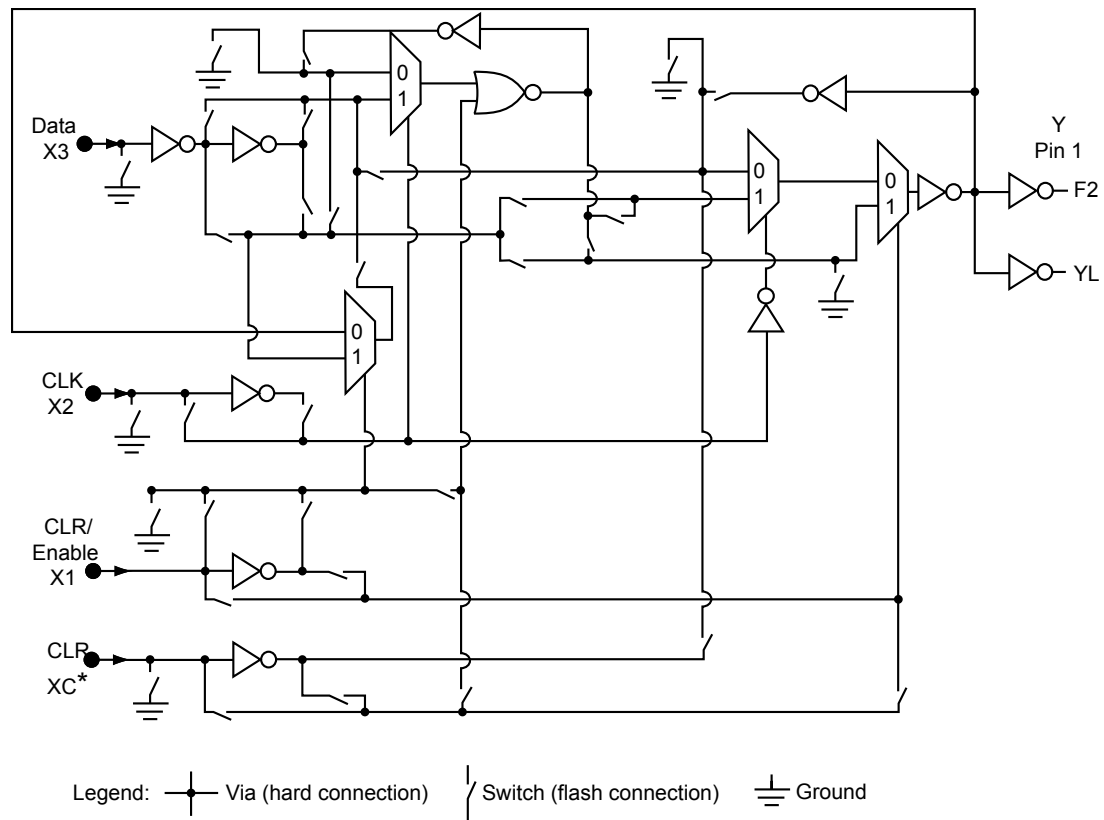
As illustrated in Figure 1-8, there are four inputs in a logic VersaTile cell, and each VersaTile can be configured using the appropriate flash switch connections:

- Any 3-input logic function
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set (on a 4th input)

VersaTiles can flexibly map the logic and sequential gates of a design. The inputs of the VersaTile can be inverted (allowing bubble pushing), and the output of the tile can connect to high-speed, very-long-line routing resources. VersaTiles and larger functions can be connected with any of the four levels of routing hierarchy.

When the VersaTile is used as an enable D-flip-flop, SET/CLR is supported by a fourth input. The SET/CLR signal can only be routed to this fourth input over the VersaNet (global) network. However, if, in the user's design, the SET/CLR signal is not routed over the VersaNet network, a compile warning message will be given, and the intended logic function will be implemented by two VersaTiles instead of one.

The output of the VersaTile is F2 when the connection is to the ultra-fast local lines, or YL when the connection is to the efficient long-line or very-long-line resources.



* This input can only be connected to the global clock distribution network.

Figure 1-8 • Low Power Flash Device Core VersaTile

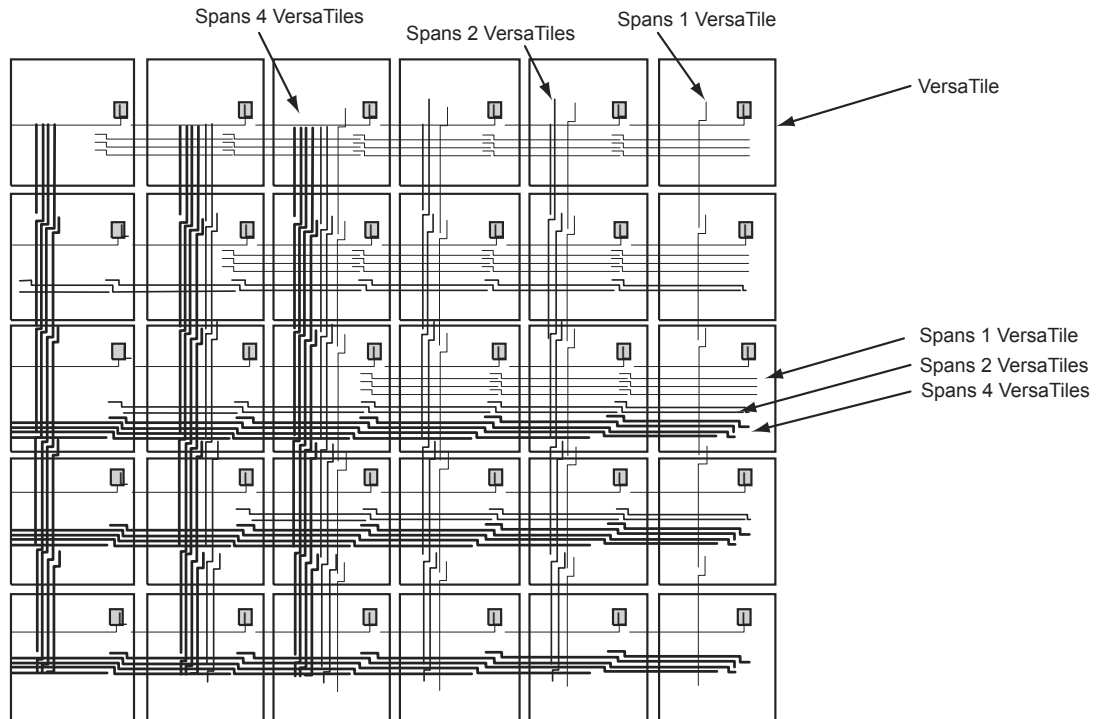


Figure 1-11 • Efficient Long-Line Resources

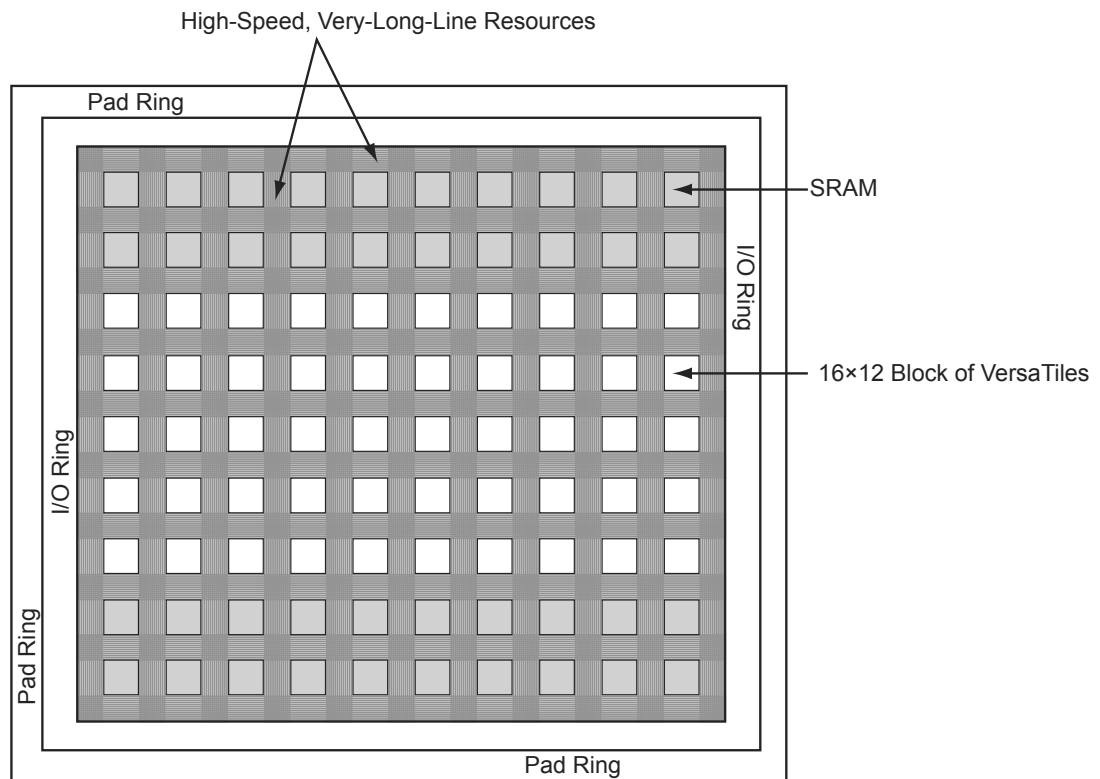


Figure 1-12 • Very-Long-Line Resources

Figure 3-18 • Globals Management GUI in Designer

3. Occasionally, the synthesis tool assigns a global macro to clock nets, even though the fanout is significantly less than other asynchronous signals. Select **Demote global nets whose fanout is less than** and enter a reasonable value for fanouts. This frees up some global networks from the signals that have very low fanouts. This can also be done using PDC.
4. Use a local clock network for the signals that do not need to go to the whole chip but should have low skew. This local clock network assignment can only be done using PDC.
5. Assign the I/O buffer using MVN if you have fixed I/O assignment. As shown in Figure 3-10 on page 45, there are three sets of global pins that have a hardwired connection to each global network. Do not try to put multiple CLKBUF macros in these three sets of global pins. For example, do not assign two CLKBUFs to GAA0x and GAA2x pins.
6. You must click **Commit** at the end of MVN assignment. This runs the pre-layout checker and checks the validity of global assignment.
7. Always run Compile with the **Keep existing physical constraints** option on. This uses the quadrant clock network assignment in the MVN assignment and checks if you have the desired signals on the global networks.
8. Run Layout and check the timing.

Using Spines of Occupied Global Networks

When a signal is assigned to a global network, the flash switches are programmed to set the MUX select lines (explained in the "Clock Aggregation Architecture" section on page 45) to drive the spines of that network with the global net. However, if the global net is restricted from reaching into the scope of a spine, the MUX drivers of that spine are available for other high-fanout or critical signals (Figure 3-20).

For example, if you want to limit the CLK1_c signal to the left half of the chip and want to use the right side of the same global network for CLK2_c, you can add the following PDC commands:

```
define_region -name region1 -type inclusive 0 0 34 29  
assign_net_macros region1 CLK1_c  
assign_local_clock -net CLK2_c -type chip B2
```

Figure 3-20 • Design Example Using Spines of Occupied Global Networks

Conclusion

IGLOO, Fusion, and ProASIC3 devices contain 18 global networks: 6 chip global networks and 12 quadrant global networks. These global networks can be segmented into local low-skew networks called spines. The spines provide low-skew networks for the high-fanout signals of a design. These allow you up to 252 different internal/external clocks in an A3PE3000 device. This document describes the architecture for the global network, plus guidelines and methodologies in assigning signals to globals and spines.

Related Documents

User's Guides

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide
http://www.microsemi.com/soc/documents/pa3_libguide_ug.pdf

Device-Specific Layout

Two kinds of CCCs are offered in low power flash devices: CCCs with integrated PLLs, and CCCs without integrated PLLs (simplified CCCs). Table 4-5 lists the number of CCCs in various devices.

Table 4-5 • Number of CCCs by Device Size and Package

| Device | | Package | CCCs with Integrated PLLs | CCCs without Integrated PLLs (simplified CCC) |
|----------------------------|----------------|--------------------|---------------------------|---|
| ProASIC3 | IGLOO | | | |
| A3PN010 | AGLN010 | All | 0 | 2 |
| A3PN015 | AGLN015 | All | 0 | 2 |
| A3PN020 | AGLN020 | All | 0 | 2 |
| | AGLN060 | CS81 | 0 | 6 |
| A3PN060 | AGLN060 | All other packages | 1 | 5 |
| | AGLN125 | CS81 | 0 | 6 |
| A3PN125 | AGLN125 | All other packages | 1 | 5 |
| | AGLN250 | CS81 | 0 | 6 |
| A3PN250 | AGLN250 | All other packages | 1 | 5 |
| A3P015 | AGL015 | All | 0 | 2 |
| A3P030 | AGL030/AGLP030 | All | 0 | 2 |
| | AGL060/AGLP060 | CS121/CS201 | 0 | 6 |
| A3P060 | AGL060/AGLP060 | All other packages | 1 | 5 |
| A3P125 | AGL125/AGLP125 | All | 1 | 5 |
| A3P250/L | AGL250 | All | 1 | 5 |
| A3P400 | AGL400 | All | 1 | 5 |
| A3P600/L | AGL600 | All | 1 | 5 |
| A3P1000/L | AGL1000 | All | 1 | 5 |
| A3PE600 | AGLE600 | PQ208 | 2 | 4 |
| A3PE600/L | | All other packages | 6 | 0 |
| A3PE1500 | | PQ208 | 2 | 4 |
| A3PE1500 | | All other packages | 6 | 0 |
| A3PE3000/L | | PQ208 | 2 | 4 |
| A3PE3000/L | AGLE3000 | All other packages | 6 | 0 |
| Fusion Devices | | | | |
| AFS090 | | All | 1 | 5 |
| AFS250, M1AFS250 | | All | 1 | 5 |
| AFS600, M7AFS600, M1AFS600 | | All | 2 | 4 |
| AFS1500, M1AFS1500 | | All | 2 | 4 |

Note: nano 10 k, 15 k, and 20 k offer 6 global MUXes instead of CCCs.

```
DYNCCC Core(.CLKA(CLKA), .EXTFB(GND), .POWERDOWN(POWERDOWN), .GLA(GLA), .LOCK(LOCK),
.CLKB(CLKB), .GLB(GLB), .YB(), .CLKC(CLKC), .GLC(GLC), .YC(), .SDIN(SDIN),
.SCLK(SCLK), .SShift(SShift), .SUPDATE(SUPDATE), .MODE(MODE), .SDOUT(SDOUT),
.OADIV0(GND), .OADIV1(GND), .OADIV2(VCC), .OADIV3(GND), .OADIV4(GND), .OAMUX0(GND),
.OAMUX1(GND), .OAMUX2(VCC), .DLYGLA0(GND), .DLYGLA1(GND), .DLYGLA2(GND),
.DLYGLA3(GND), .DLYGLA4(GND), .OBDIV0(GND), .OBDIV1(GND), .OBDIV2(GND),
.OBDIV3(GND), .OBDIV4(GND), .OBMUX0(GND), .OBMUX1(GND), .OBMUX2(GND), .DLYYB0(GND),
.DLYYB1(GND), .DLYYB2(GND), .DLYYB3(GND), .DLYYB4(GND), .DLYGLB0(GND),
.DLYGLB1(GND), .DLYGLB2(GND), .DLYGLB3(GND), .DLYGLB4(GND), .OCDIV0(GND),
.OCDIV1(GND), .OCDIV2(GND), .OCDIV3(GND), .OCDIV4(GND), .OCMUX0(GND), .OCMUX1(GND),
.OCMUX2(GND), .DLYYC0(GND), .DLYYC1(GND), .DLYYC2(GND), .DLYYC3(GND), .DLYYC4(GND),
.DLYGLC0(GND), .DLYGLC1(GND), .DLYGLC2(GND), .DLYGLC3(GND), .DLYGLC4(GND),
.FINDIV0(VCC), .FINDIV1(GND), .FINDIV2(VCC), .FINDIV3(GND), .FINDIV4(GND),
.FINDIV5(GND), .FINDIV6(GND), .FBDIV0(GND), .FBDIV1(GND), .FBDIV2(GND),
.FBDIV3(GND), .FBDIV4(GND), .FBDIV5(VCC), .FBDIV6(GND), .FBDLY0(GND), .FBDLY1(GND),
.FBDLY2(GND), .FBDLY3(GND), .FBDLY4(GND), .FBSEL0(VCC), .FBSEL1(GND),
.XDLYSEL(GND), .VCOSEL0(GND), .VCOSEL1(GND), .VCOSEL2(VCC));
defparam Core.VCOFREQUENCY = 165.000;

endmodule
```

Delayed Clock Configuration

The CLKDLY macro can be generated with the desired delay and input clock source (Hardwired I/O, External I/O, or Core Logic), as in Figure 4-28.

Figure 4-28 • Delayed Clock Configuration Dialog Box

After setting all the required parameters, users can generate one or more PLL configurations with HDL or EDIF descriptions by clicking the **Generate** button. SmartGen gives the option of saving session results and messages in a log file:

```
*****
Macro Parameters
*****
```

| | |
|---------------|-----------------|
| Name | : delay_macro |
| Family | : ProASIC3 |
| Output Format | : Verilog |
| Type | : Delayed Clock |
| Delay Index | : 2 |
| CLKA Source | : Hardwired I/O |

Total Clock Delay = 0.935 ns.

The resultant CLKDLY macro Verilog netlist is as follows:

```
module delay_macro(GL,CLK);

output GL;
input CLK;
```

- Use quadrant global region assignments by finding the clock net associated with the CCC macro under the Nets tab and creating a quadrant global region for the net, as shown in Figure 4-33.
-

Figure 4-33 • Quadrant Clock Assignment for a Global Net

External I/O–Driven CCCs

The above-mentioned recommendation for proper layout techniques will ensure the correct assignment. It is possible that, especially with External I/O–Driven CCC macros, placement of the CCC macro in a desired location may not be achieved. For example, assigning an input port of an External I/O–Driven CCC near a particular CCC location does not guarantee global assignments to the desired location. This is because the clock inputs of External I/O–Driven CCCs can be assigned to any I/O location; therefore, it is possible that the CCC connected to the clock input will be routed to a location other than the one closest to the I/O location, depending on resource availability and placement constraints.

Clock Placer

The clock placer is a placement engine for low power flash devices that places global signals on the chip global and quadrant global networks. Based on the clock assignment constraints for the chip global and quadrant global clocks, it will try to satisfy all constraints, as well as creating quadrant clock regions when necessary. If the clock placer fails to create the quadrant clock regions for the global signals, it will report an error and stop Layout.

The user must ensure that the constraints set to promote clock signals to quadrant global networks are valid.

Cascading CCCs

The CCCs in low power flash devices can be cascaded. Cascading CCCs can help achieve more accurate PLL output frequency results than those achievable with a single CCC. In addition, this technique is useful when the user application requires the output clock of the PLL to be a multiple of the reference clock by an integer greater than the maximum feedback divider value of the PLL (divide by 128) to achieve the desired frequency.

For example, the user application may require a 280 MHz output clock using a 2 MHz input reference clock, as shown in Figure 4-34 on page 110.

Recommended Board-Level Considerations

The power to the PLL core is supplied by VCCPLA/B/C/D/E/F (VCCPLx), and the associated ground connections are supplied by VCOMPLA/B/C/D/E/F (VCOMPLx). When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Optionally, the PLL can be turned on/off during normal device operation via the POWERDOWN port (see Table 4-3 on page 68).

PLL Power Supply Decoupling Scheme

The PLL core is designed to tolerate noise levels on the PLL power supply as specified in the datasheets. When operated within the noise limits, the PLL will meet the output peak-to-peak jitter specifications specified in the datasheets. User applications should always ensure the PLL power supply is powered from a noise-free or low-noise power source.

However, in situations where the PLL power supply noise level is higher than the tolerable limits, various decoupling schemes can be designed to suppress noise to the PLL power supply. An example is provided in Figure 4-38. The VCCPLx and VCOMPLx pins correspond to the PLL analog power supply and ground.

Microsemi strongly recommends that two ceramic capacitors (10 nF in parallel with 100 nF) be placed close to the power pins (less than 1 inch away). A third generic 10 μ F electrolytic capacitor is recommended for low-frequency noise and should be placed farther away due to its large physical size. Microsemi recommends that a 6.8 μ H inductor be placed between the supply source and the capacitors to filter out any low-/medium- and high-frequency noise. In addition, the PCB layers should be controlled so the VCCPLx and VCOMPLx planes have the minimum separation possible, thus generating a good-quality RF capacitor.

For more recommendations, refer to the *Board-Level Considerations* application note.

Recommended 100 nF capacitor:

- Producer BC Components, type X7R, 100 nF, 16 V
- BC Components part number: 0603B104K160BT
- Digi-Key part number: BC1254CT-ND
- Digi-Key part number: BC1254TR-ND

Recommended 10 nF capacitor:

- Surface-mount ceramic capacitor
- Producer BC Components, type X7R, 10 nF, 50 V
- BC Components part number: 0603B103K500BT
- Digi-Key part number: BC1252CT-ND
- Digi-Key part number: BC1252TR-ND

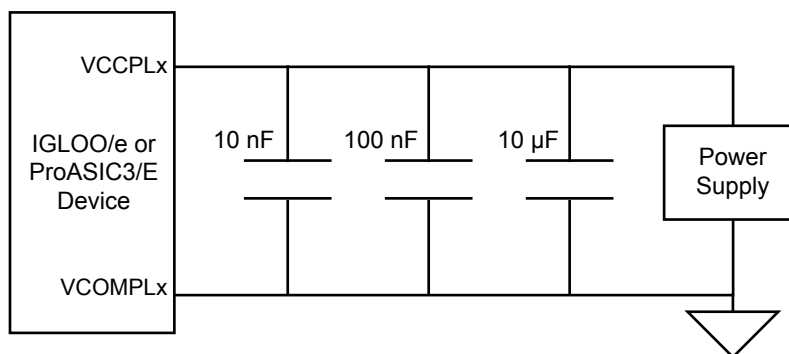


Figure 4-38 • Decoupling Scheme for One PLL (should be replicated for each PLL used)

6 – SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Introduction

As design complexity grows, greater demands are placed upon an FPGA's embedded memory. Fusion, IGLOO, and ProASIC3 devices provide the flexibility of true dual-port and two-port SRAM blocks. The embedded memory, along with built-in, dedicated FIFO control logic, can be used to create cascading RAM blocks and FIFOs without using additional logic gates.

IGLOO, IGLOO PLUS, and ProASIC3L FPGAs contain an additional feature that allows the device to be put in a low power mode called Flash*Freeze. In this mode, the core draws minimal power (on the order of 2 to 127 μ W) and still retains values on the embedded SRAM/FIFO and registers. Flash*Freeze technology allows the user to switch to Active mode on demand, thus simplifying power management and the use of SRAM/FIFOs.

Device Architecture

The low power flash devices feature up to 504 kbits of RAM in 4,608-bit blocks (Figure 6-1 on page 132 and Figure 6-2 on page 133). The total embedded SRAM for each device can be found in the datasheets. These memory blocks are arranged along the top and bottom of the device to allow better access from the core and I/O (in some devices, they are only available on the north side of the device). Every RAM block has a flexible, hardwired, embedded FIFO controller, enabling the user to implement efficient FIFOs without sacrificing user gates.

In the IGLOO and ProASIC3 families of devices, the following memories are supported:

- 30 k gate devices and smaller do not support SRAM and FIFO.
- 60 k and 125 k gate devices support memories on the north side of the device only.
- 250 k devices and larger support memories on the north and south sides of the device.

In Fusion devices, the following memories are supported:

- AFS090 and AFS250 support memories on the north side of the device only.
- AFS600 and AFS1500 support memories on the north and south sides of the device.

SRAM and FIFO Architecture

To meet the needs of high-performance designs, the memory blocks operate strictly in synchronous mode for both read and write operations. The read and write clocks are completely independent, and each can operate at any desired frequency up to 250 MHz.

- 4k×1, 2k×2, 1k×4, 512×9 (dual-port RAM—2 read / 2 write or 1 read / 1 write)
- 512×9, 256×18 (2-port RAM—1 read / 1 write)
- Sync write, sync pipelined / nonpipelined read

Automotive ProASIC3 devices support single-port SRAM capabilities or dual-port SRAM only under specific conditions. Dual-port mode is supported if the clocks to the two SRAM ports are the same and 180° out of phase (i.e., the port A clock is the inverse of the port B clock). The Libero SoC software macro libraries support a dual-port macro only. For use of this macro as a single-port SRAM, the inputs and clock of one port should be tied off (grounded) to prevent errors during design compile. For use in dual-port mode, the same clock with an inversion between the two clock pins of the macro should be used in the design to prevent errors during compile.

The memory block includes dedicated FIFO control logic to generate internal addresses and external flag logic (FULL, EMPTY, AFULL, AEMPTY).

Simultaneous dual-port read/write and write/write operations at the same address are allowed when certain timing requirements are met.

During RAM operation, addresses are sourced by the user logic, and the FIFO controller is ignored. In FIFO mode, the internal addresses are generated by the FIFO controller and routed to the RAM array by internal MUXes.

The low power flash device architecture enables the read and write sizes of RAMs to be organized independently, allowing for bus conversion. For example, the write size can be set to 256×18 and the read size to 512×9.

Both the write width and read width for the RAM blocks can be specified independently with the WW (write width) and RW (read width) pins. The different D×W configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1. When widths of one, two, or four are selected, the ninth bit is unused. For example, when writing nine-bit values and reading four-bit values, only the first four bits and the second four bits of each nine-bit value are addressable for read operations. The ninth bit is not accessible.

Conversely, when writing four-bit values and reading nine-bit values, the ninth bit of a read operation will be undefined. The RAM blocks employ little-endian byte order for read and write operations.

Memory Blocks and Macros

Memory blocks can be configured with many different aspect ratios, but are generically supported in the macro libraries as one of two memory elements: RAM4K9 or RAM512X18. The RAM4K9 is configured as a true dual-port memory block, and the RAM512X18 is configured as a two-port memory block. Dual-port memory allows the RAM to both read from and write to either port independently. Two-port memory allows the RAM to read from one port and write to the other using a common clock or independent read and write clocks. If needed, the RAM4K9 blocks can be configured as two-port memory blocks. The memory block can be configured as a FIFO by combining the basic memory block with dedicated FIFO controller logic. The FIFO macro is named FIFO4KX18 (Figure 6-3 on page 136).

Clocks for the RAM blocks can be driven by the VersaNet (global resources) or by regular nets. When using local clock segments, the clock segment region that encompasses the RAM blocks can drive the RAMs. In the dual-port configuration (RAM4K9), each memory block port can be driven by either rising-edge or falling-edge clocks. Each port can be driven by clocks with different edges. Though only a rising-edge clock can drive the physical block itself, the Microsemi Designer software will automatically bubble-push the inversion to properly implement the falling-edge trigger for the RAM block.

SRAM Usage

The following descriptions refer to the usage of both RAM4K9 and RAM512X18.

Clocking

The dual-port SRAM blocks are only clocked on the rising edge. SmartGen allows falling-edge-triggered clocks by adding inverters to the netlist, hence achieving dual-port SRAM blocks that are clocked on either edge (rising or falling). For dual-port SRAM, each port can be clocked on either edge and by separate clocks by port. Note that for Automotive ProASIC3, the same clock, with an inversion between the two clock pins of the macro, should be used in design to prevent errors during compile.

Low power flash devices support inversion (bubble-pushing) throughout the FPGA architecture, including the clock input to the SRAM modules. Inversions added to the SRAM clock pin on the design schematic or in the HDL code will be automatically accounted for during design compile without incurring additional delay in the clock path.

The two-port SRAM can be clocked on the rising or falling edge of WCLK and RCLK.

If negative-edge RAM and FIFO clocking is selected for memory macros, clock edge inversion management (bubble-pushing) is automatically used within the development tools, without performance penalty.

Modes of Operation

There are two read modes and one write mode:

- Read Nonpipelined (synchronous—1 clock edge): In the standard read mode, new data is driven onto the RD bus in the same clock cycle following RA and REN valid. The read address is registered on the read port clock active edge, and data appears at RD after the RAM access time. Setting PIPE to OFF enables this mode.
- Read Pipelined (synchronous—2 clock edges): The pipelined mode incurs an additional clock delay from address to data but enables operation at a much higher frequency. The read address is registered on the read port active clock edge, and the read data is registered and appears at RD after the second read clock edge. Setting PIPE to ON enables this mode.
- Write (synchronous—1 clock edge): On the write clock active edge, the write data is written into the SRAM at the write address when WEN is HIGH. The setup times of the write address, write enables, and write data are minimal with respect to the write clock.

RAM Initialization

Each SRAM block can be individually initialized on power-up by means of the JTAG port using the UJTAG mechanism. The shift register for a target block can be selected and loaded with the proper bit configuration to enable serial loading. The 4,608 bits of data can be loaded in a single operation.

FIFO Features

The FIFO4KX18 macro is created by merging the RAM block with dedicated FIFO logic (Figure 6-6 on page 142). Since the FIFO logic can only be used in conjunction with the memory block, there is no separate FIFO controller macro. As with the RAM blocks, the FIFO4KX18 nomenclature does not refer to a possible aspect ratio, but rather to the deepest possible data depth and the widest possible data width. FIFO4KX18 can be configured into the following aspect ratios: 4,096×1, 2,048×2, 1,024×4, 512×9, and 256×18. In addition to being fully synchronous, the FIFO4KX18 also has the following features:

- Four FIFO flags: Empty, Full, Almost-Empty, and Almost-Full
- Empty flag is synchronized to the read clock
- Full flag is synchronized to the write clock
- Both Almost-Empty and Almost-Full flags have programmable thresholds
- Active-low asynchronous reset
- Active-low block enable
- Active-low write enable
- Active-high read enable
- Ability to configure the FIFO to either stop counting after the empty or full states are reached or to allow the FIFO counters to continue

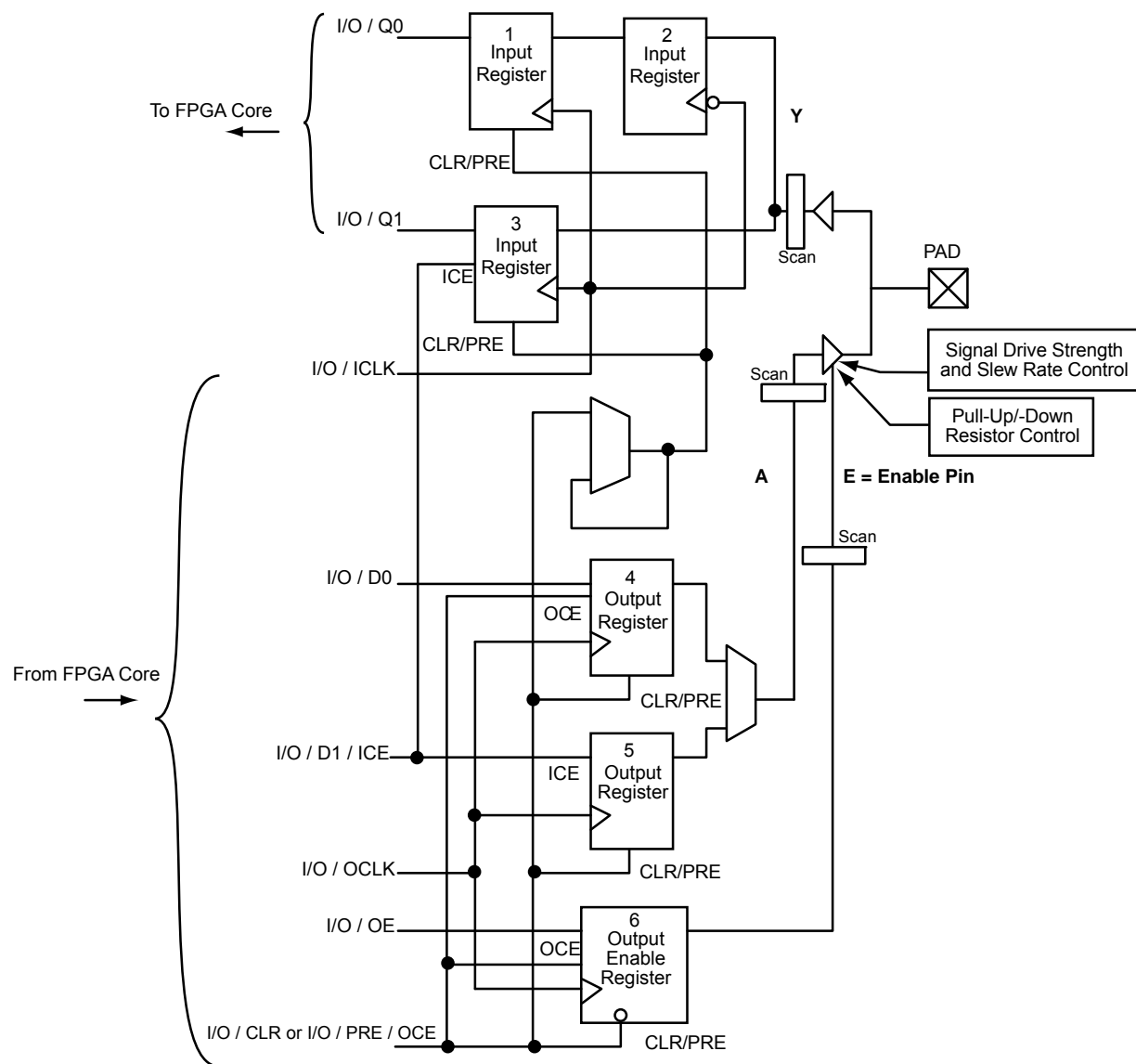


Figure 7-2 • I/O Block Logical Representation for Dual-Tile Designs (60 k,125 k, and 250 k Devices)

Table 7-10 • Hot-Swap Level 3

| | |
|---|--|
| Description | Hot-swap while bus idle |
| Power Applied to Device | Yes |
| Bus State | Held idle (no ongoing I/O processes during insertion/removal) |
| Card Ground Connection | Reset must be maintained for 1 ms before, during, and after insertion/removal. |
| Device Circuitry Connected to Bus Pins | Must remain glitch-free during power-up or power-down |
| Example Application | Board bus shared with card bus is "frozen," and there is no toggling activity on the bus. It is critical that the logic states set on the bus signal not be disturbed during card insertion/removal. |
| Compliance of nano Devices | Compliant |

Table 7-11 • Hot-Swap Level 4

| | |
|---|---|
| Description | Hot-swap on an active bus |
| Power Applied to Device | Yes |
| Bus State | Bus may have active I/O processes ongoing, but device being inserted or removed must be idle. |
| Card Ground Connection | Reset must be maintained for 1 ms before, during, and after insertion/removal. |
| Device Circuitry Connected to Bus Pins | Must remain glitch-free during power-up or power-down |
| Example Application | There is activity on the system bus, and it is critical that the logic states set on the bus signal not be disturbed during card insertion/removal. |
| Compliance of nano Devices | Compliant |

For Level 3 and Level 4 compliance with the nano devices, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

Example 2 (low–medium speed, medium current):

$$R_{tx_out_high} = R_{tx_out_low} = 10 \, \Omega$$

$$R1 = 220 \, \Omega (\pm 5\%), P(r1)_{min} = 0.018 \, \Omega$$

$$R2 = 390 \, \Omega (\pm 5\%), P(r2)_{min} = 0.032 \, \Omega$$

$$I_{max_tx} = 5.5 \, V / (220 \times 0.95 + 390 \times 0.95 + 10) = 9.17 \, mA$$

$$t_{RISE} = t_{FALL} = 4 \, ns \text{ at } C_{pad_load} = 10 \, pF \text{ (includes up to 25\% safety margin)}$$

$$t_{RISE} = t_{FALL} = 20 \, ns \text{ at } C_{pad_load} = 50 \, pF \text{ (includes up to 25\% safety margin)}$$

Other values of resistors are also allowed as long as the resistors are sized appropriately to limit the voltage at the receiving end to $2.5 \, V < V_{in} (rx) < 3.6 \, V$ when the transmitter sends a logic 1. This range of $V_{in_dc}(rx)$ must be assured for any combination of transmitter supply ($5 \, V \pm 0.5 \, V$), transmitter output resistance, and board resistor tolerances.

Temporary overshoots are allowed according to the overshoot and undershoot table in the datasheet.

Solution 1

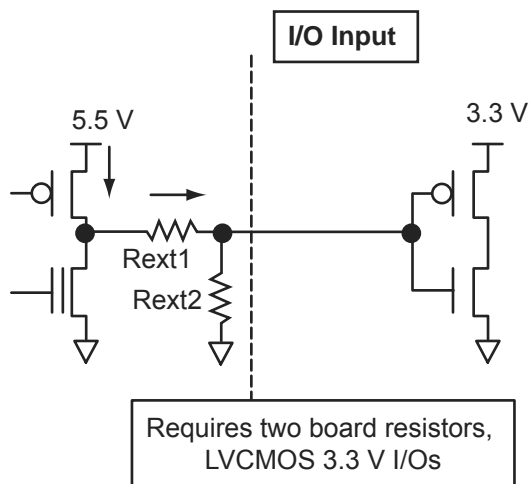


Figure 7-5 • Solution 1

those banks, the user does not need to assign the same VCCI voltage to another bank. The user needs to assign the other three VCCI voltages to three more banks.

Assigning Technologies and VREF to I/O Banks

Low power flash devices offer a wide variety of I/O standards, including voltage-referenced standards. Before proceeding to Layout, each bank must have the required VCCI voltage assigned for the corresponding I/O technologies used for that bank. The voltage-referenced standards require the use of a reference voltage (VREF). This assignment can be done manually or automatically. The following sections describe this in detail.

Manually Assigning Technologies to I/O Banks

The user can import the PDC at this point and resolve this requirement. The PDC command is

```
set_iobank [bank name] -vcci [vcci value]
```

Another method is to use the I/O Bank Settings dialog box (**MVN > Edit > I/O Bank Settings**) to set up the V_{CCI} voltage for the bank (Figure 8-12).

Figure 8-12 • Setting VCCI for a Bank

```
module ddr_test(DIN, CLK, CLR, DOUT);

input  DIN, CLK, CLR;
output DOUT;

  Inbuf_ddr Inbuf_ddr (.PAD(DIN), .CLR(clr), .CLK(clk), .QR(qr), .QF(qf));
  Outbuf_ddr Outbuf_ddr (.DataR(qr), .DataF(qf), .CLR(clr), .CLK(clk), .PAD(DOUT));

  INBUF INBUF_CLR (.PAD(CLR), .Y(clr));
  INBUF INBUF_CLK (.PAD(CLK), .Y(clk));

endmodule
```

Simulation Consideration

Microsemi DDR simulation models use inertial delay modeling by default (versus transport delay modeling). As such, pulses that are shorter than the actual gate delays should be avoided, as they will not be seen by the simulator and may be an issue in post-routed simulations. The user must be aware of the default delay modeling and must set the correct delay model in the simulator as needed.

Conclusion

Fusion, IGLOO, and ProASIC3 devices support a wide range of DDR applications with different I/O standards and include built-in DDR macros. The powerful capabilities provided by SmartGen and its GUI can simplify the process of including DDR macros in designs and minimize design errors. Additional considerations should be taken into account by the designer in design floorplanning and placement of I/O flip-flops to minimize datapath skew and to help improve system timing margins. Other system-related issues to consider include PLL and clock partitioning.

IEEE 1532 (JTAG) Interface

The supported industry-standard IEEE 1532 programming interface builds on the IEEE 1149.1 (JTAG) standard. IEEE 1532 defines the standardized process and methodology for ISP. Both silicon and software issues are addressed in IEEE 1532 to create a simplified ISP environment. Any IEEE 1532 compliant programmer can be used to program low power flash devices. Device serialization is not supported when using the IEEE1532 standard. Refer to the standard for detailed information about IEEE 1532.

Security

Unlike SRAM-based FPGAs that require loading at power-up from an external source such as a microcontroller or boot PROM, Microsemi nonvolatile devices are live at power-up, and there is no bitstream required to load the device when power is applied. The unique flash-based architecture prevents reverse engineering of the programmed code on the device, because the programmed data is stored in nonvolatile memory cells. Each nonvolatile memory cell is made up of small capacitors and any physical deconstruction of the device will disrupt stored electrical charges.

Each low power flash device has a built-in 128-bit Advanced Encryption Standard (AES) decryption core, except for the 30 k gate devices and smaller. Any FPGA core or FlashROM content loaded into the device can optionally be sent as encrypted bitstream and decrypted as it is loaded. This is particularly suitable for applications where device updates must be transmitted over an unsecured network such as the Internet. The embedded AES decryption core can prevent sensitive data from being intercepted (Figure 12-1 on page 265). A single 128-bit AES Key (32 hex characters) is used to encrypt FPGA core programming data and/or FlashROM programming data in the Microsemi tools. The low power flash devices also decrypt with a single 128-bit AES Key. In addition, low power flash devices support a Message Authentication Code (MAC) for authentication of the encrypted bitstream on-chip. This allows the encrypted bitstream to be authenticated and prevents erroneous data from being programmed into the device. The FPGA core, FlashROM, and Flash Memory Blocks (FBs), in Fusion only, can be updated independently using a programming file that is AES-encrypted (cipher text) or uses plain text.

3. A single STAPL file or multiple STAPL files with multiple FlashROM contents. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
4. A single STAPL file to configure the security settings for the device, such as the AES Key and/or Pass Key.

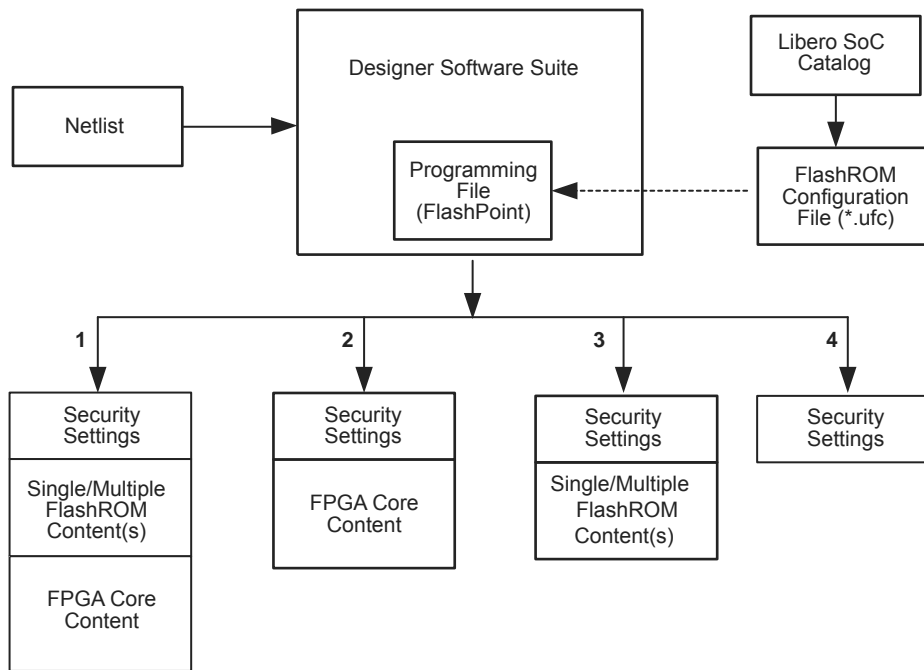


Figure 12-4 • Flexible Programming File Generation for Different Applications

Programming Solution

For device programming, any IEEE 1532-compliant programmer can be used; however, the FlashPro4/3/3X programmer must be used to control the low power flash device's rich security features and FlashROM programming options. The FlashPro4/3/3X programmer is a low-cost portable programmer for the Microsemi flash families. It can also be used with a powered USB hub for parallel programming. General specifications for the FlashPro4/3/3X programmer are as follows:

- Programming clock – TCK is used with a maximum frequency of 20 MHz, and the default frequency is 4 MHz.
- Programming file – STAPL
- Daisy chain – Supported. You can use the ChainBuilder software to build the programming file for the chain.
- Parallel programming – Supported. Multiple FlashPro4/3/3X programmers can be connected together using a powered USB hub or through the multiple USB ports on the PC.
- Power supply – The target board must provide VCC, VCCI, VPUMP, and VJTAG during programming. However, if there is only one device on the target board, the FlashPro4/3/3X programmer can generate the required VPUMP voltage from the USB port.

2. VCC rises to 1.5 V before programming begins.
-

Figure 13-3 • Programming Algorithm

The oscilloscope plot in Figure 13-3 shows a wider time interval for the programming algorithm and includes the TDI and TMS signals from the FlashPro3. These signals carry the programming information that is programmed into the device and should only start toggling after the V_{CC} core voltage reaches 1.5 V. Again, TRST from FlashPro3 and the V_{CC} core voltage of the IGLOO device are labeled. As shown in Figure 13-3, TDI and TMS are floating initially, and the core voltage is 1.2 V. When a programming command on the FlashPro3 is executed, TRST is driven HIGH and TDI is momentarily driven to ground. In response to the HIGH TRST signal, the circuit responds and pulls the core voltage to 1.5 V. After 100 ms, TRST is briefly driven LOW by the FlashPro software. This is expected behavior that ensures the device JTAG state machine is in Reset prior to programming. TRST remains HIGH for the duration of the programming. It can be seen in Figure 13-3 that the VCC core voltage signal remains at 1.5 V for approximately 50 ms before information starts passing through on TDI and TMS. This confirms that the voltage switching circuit drives the VCC core supply voltage to 1.5 V prior to programming.

Microsemi's Flash Devices Support the JTAG Feature

The flash-based FPGAs listed in Table 15-1 support the JTAG feature and the functions described in this document.

Table 15-1 • Flash-Based FPGAs

| Series | Family* | Description |
|----------|----------------------|--|
| IGLOO | IGLOO | Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology |
| | IGLOOe | Higher density IGLOO FPGAs with six PLLs and additional I/O standards |
| | IGLOO nano | The industry's lowest-power, smallest-size solution |
| | IGLOO PLUS | IGLOO FPGAs with enhanced I/O capabilities |
| ProASIC3 | ProASIC3 | Low power, high-performance 1.5 V FPGAs |
| | ProASIC3E | Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards |
| | ProASIC3 nano | Lowest-cost solution with enhanced I/O capabilities |
| | ProASIC3L | ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology |
| | RT ProASIC3 | Radiation-tolerant RT3PE600L and RT3PE3000L |
| | Military ProASIC3/EL | Military temperature A3PE600L, A3P1000, and A3PE3000L |
| | Automotive ProASIC3 | ProASIC3 FPGAs qualified for automotive applications |
| Fusion | Fusion | Mixed signal FPGA integrating ProASIC®3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device |

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 15-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 15-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.